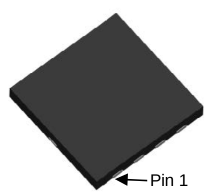
P-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω) Max.	I_D (A)	Q_g (Typ.)
- 30	0.015 at V_{GS} = - 10 V	- 40[d]	45.1 nC
	0.024 at V_{GS} = - 4.5 V	- 30[d]	

DFN 3x3 EP

Top View



Bottom View

FEATURES

- TrenchFET® Power MOSFET
- Low On-Resistance for Low Voltage Drop
- 100 % R_g and UIS Tested

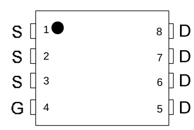
RoHS COMPLIANT

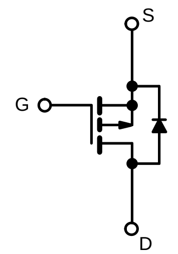
HALOGEN FREE

APPLICATIONS

- Battery, Load and Adaptor Switches
  - Notebook Computers
  - Notebook Battery Packs

Top View





P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	- 30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	- 40[d]	A
	T_C = 70 °C		- 30[d]	
	T_A = 25 °C		- 14.7[a, b]	
	T_A = 70 °C		- 9.1[a, b]	
Pulsed Drain Current (t = 100 µs)		I_{DM}	- 160	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	- 40[d]	
	T_A = 25 °C		- 3.1[a, b]	
Avalanche Current	L = 0.1 mH	I_{AS}	- 23	
Single-Pulse Avalanche Energy		E_{AS}	35.2	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	52	W
	T_C = 70 °C		33	
	T_A = 25 °C		5.2[a, b]	
	T_A = 70 °C		3.2[a, b]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature)[e, f]			265	

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[a, c]	t ≤ 10 s	R_{thJA}	21	30	°C/W
Maximum Junction-to-Case	Steady State	R_{thJC}	2.1	2.7	

Notes:

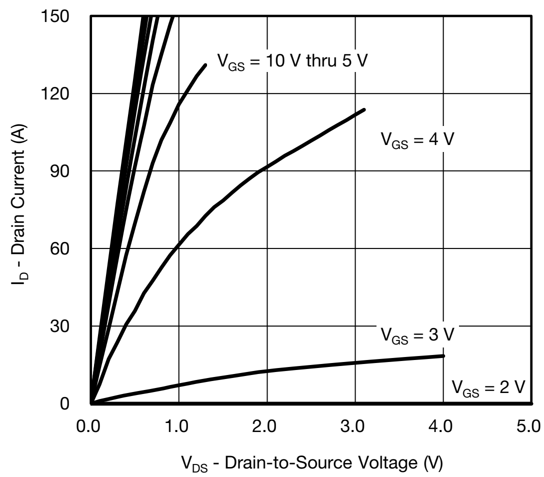
a. Surface mounted on 1" x 1" FR4 board.
b. t = 10 s.
c. Maximum under steady state conditions is 70 °C/W.
d. Package limited.
e. The DFN3X3 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0, I_D = - 250 µA	- 30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = - 250 µA		- 22		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			4.1		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 1		- 3	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 24 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 24 V, V_{GS} = 0 V, T_J = 55 °C			- 5	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ - 10 V, V_{GS} = - 10 V	- 40			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 10 V, I_D = - 15 A		0.015	0.018	Ω
		V_{GS} = - 4.5 V, I_D = - 10 A		0.024	0.027	
Forward Transconductance[a]	g_{fs}	V_{DS} = - 10 V, I_D = - 15 A		60		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = - 15 V, V_{GS} = 0 V, f = 1 MHz		2150		pF
Output Capacitance	C_{oss}			570		
Reverse Transfer Capacitance	C_{rss}			483		
Total Gate Charge	Q_g	V_{DS} = - 15 V, V_{GS} = - 10 V, I_D = - 10 A		80	135	nC
		V_{DS} = - 15 V, V_{GS} = - 4.5 V, I_D = - 10 A		45.1	65	
Gate-Source Charge	Q_{gs}			13.6		
Gate-Drain Charge	Q_{gd}			28.8		
Gate Resistance	R_g	f = 1 MHz	0.5	2.3	4.9	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 15 V, R_L = 1.5 Ω $I_D \cong$ - 10 A, V_{GEN} = - 10 V, R_g = 1 Ω		14	30	ns
Rise Time	t_r			12	24	
Turn-Off DelayTime	$t_{d(off)}$			59	110	
Fall Time	t_f			11	24	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 15 V, R_L = 1.5 Ω $I_D \cong$ - 10 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		59	120	
Rise Time	t_r			60	120	
Turn-Off DelayTime	$t_{d(off)}$			52	100	
Fall Time	t_f			27	52	
Drain-Source Body Diode Characteristics						
Continous Source-Drain Diode Current	I_S	T_C = 25 °C			- 40	A
Pulse Diode Forward Current (100 µs)	I_{SM}				- 160	
Body Diode Voltage	V_{SD}	I_S = - 3 A, V_{GS} = 0		- 0.74	- 1.20	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = - 10 A, dI/dt = 100 A/µs, T_J = 25 °C		23	46	ns
Body Diode Reverse Recovery Charge	Q_{rr}			12	24	nC
Reverse Recovery Fall Time	t_a			9		ns
Reverse Recovery Rise Time	t_b			14		

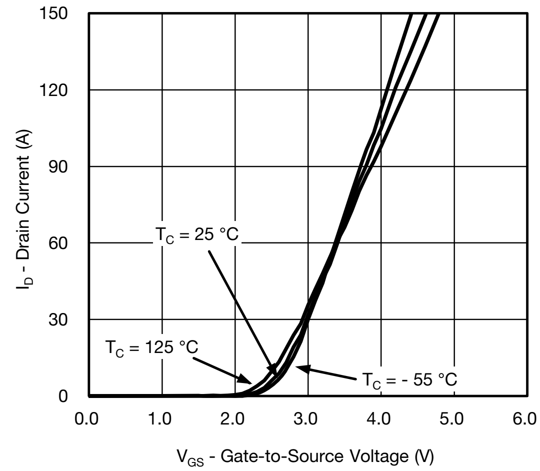
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

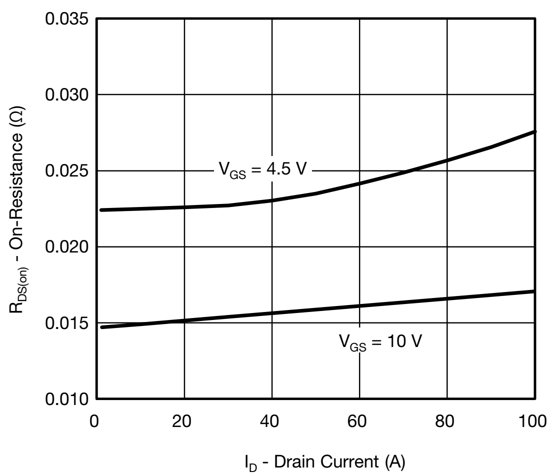
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



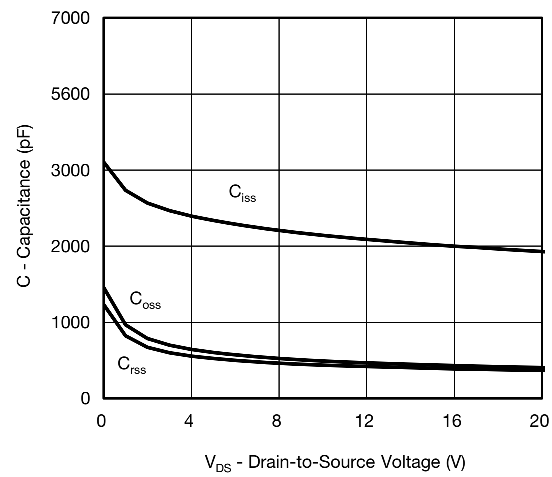
Output Characteristics



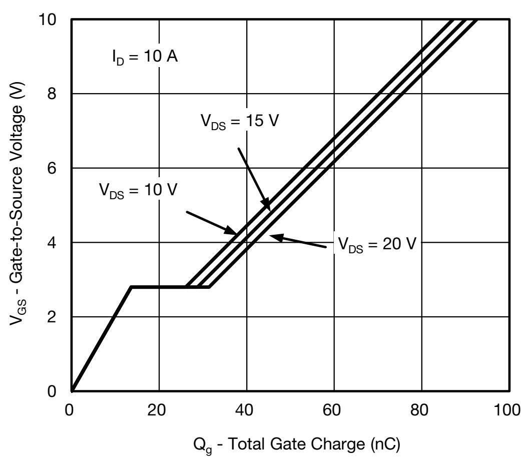
Transfer Characteristics



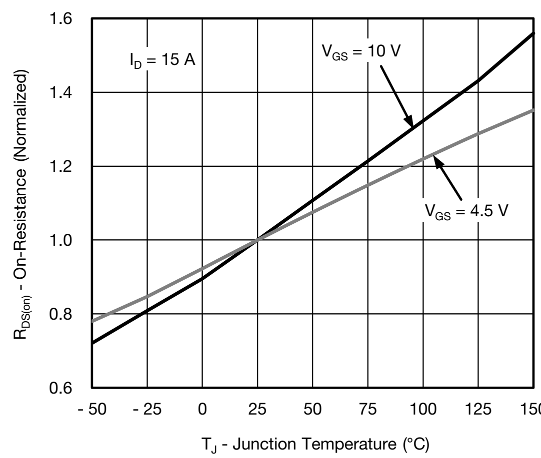
On-Resistance vs. Drain Current



Capacitance

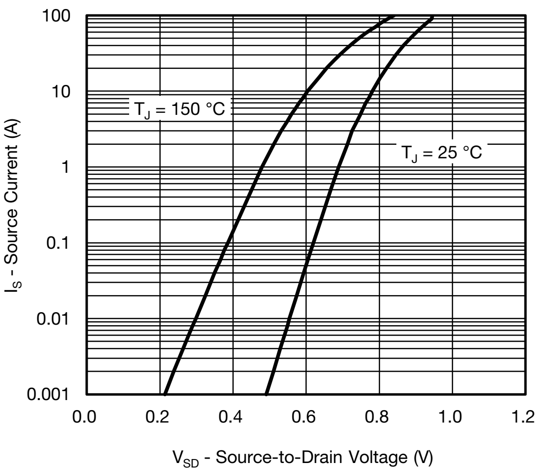


Gate Charge

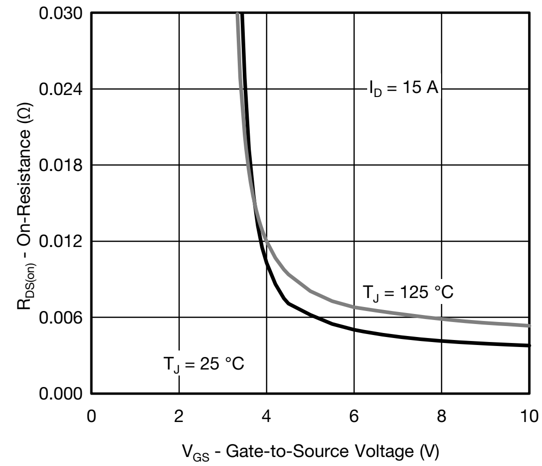


On-Resistance vs. Junction Temperature

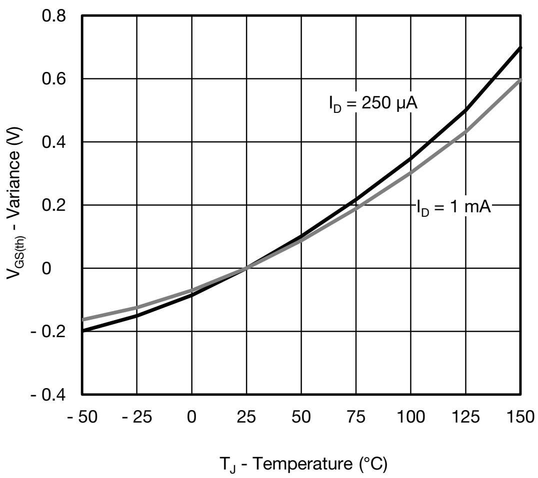
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



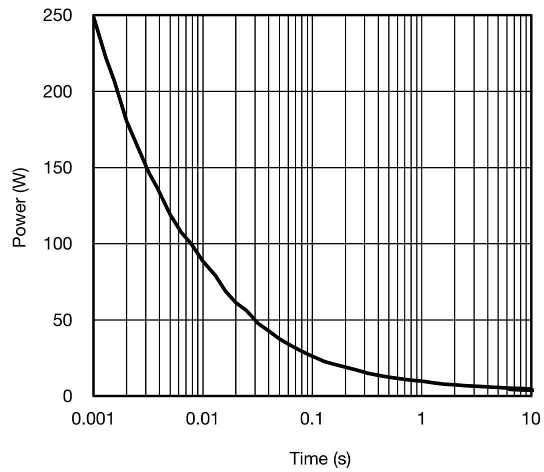
Source-Drain Diode Forward Voltage



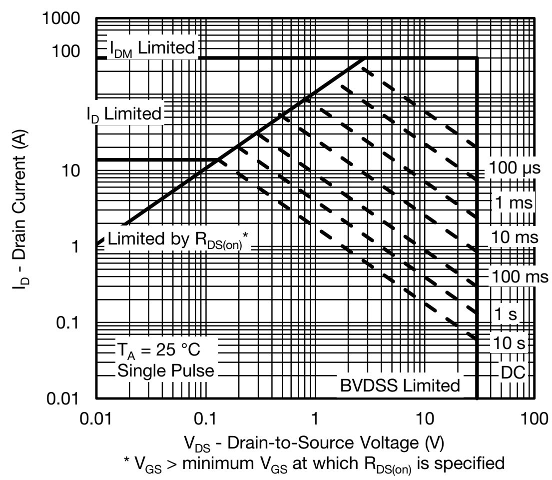
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

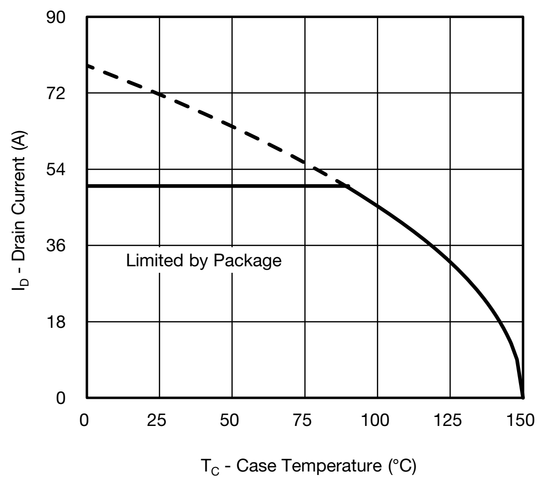


Single Pulse Power, Junction-to-Ambient

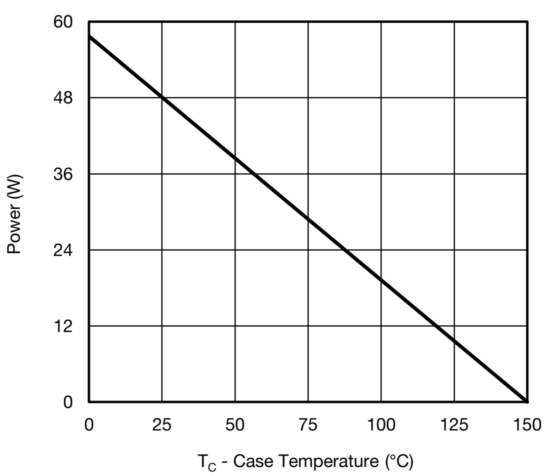


Safe Operating Area

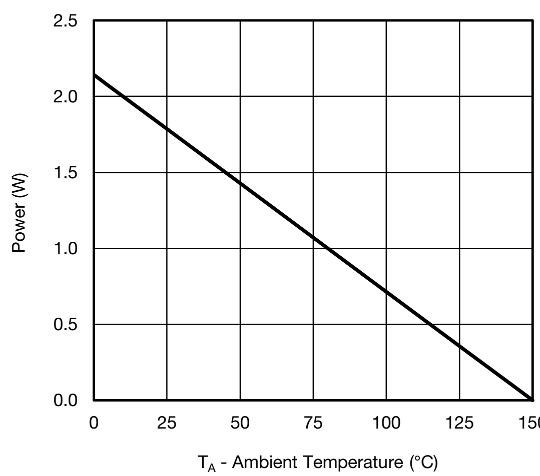
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



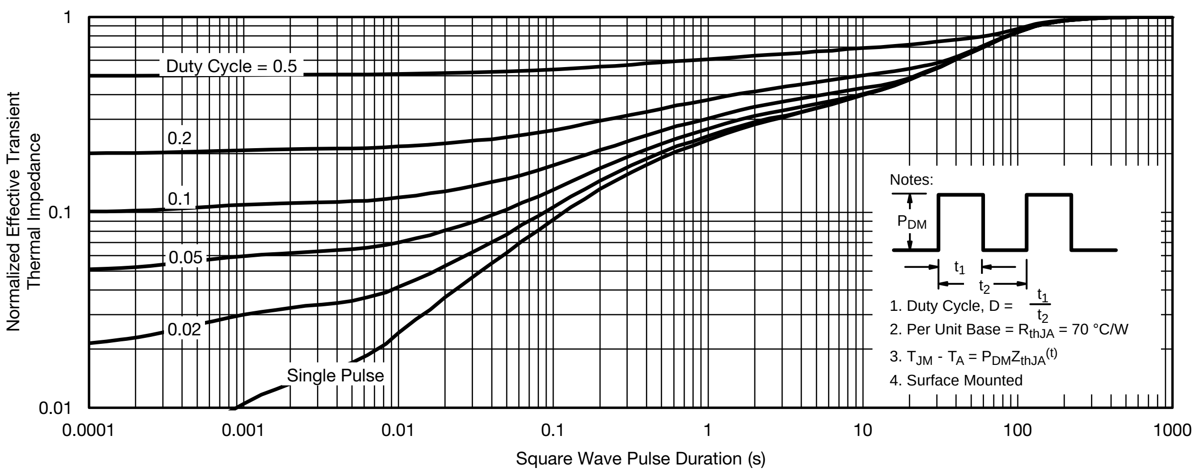
Power, Junction-to-Case



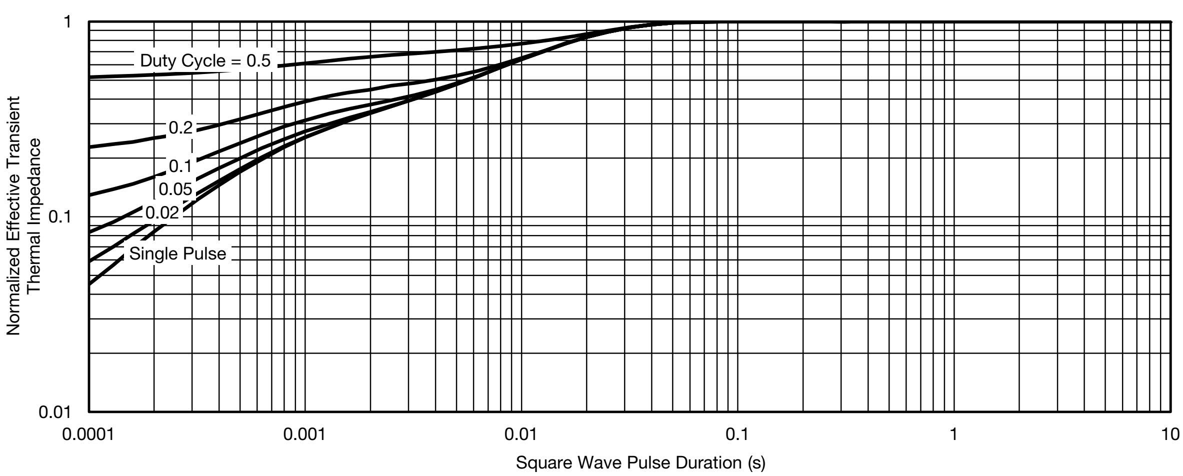
Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

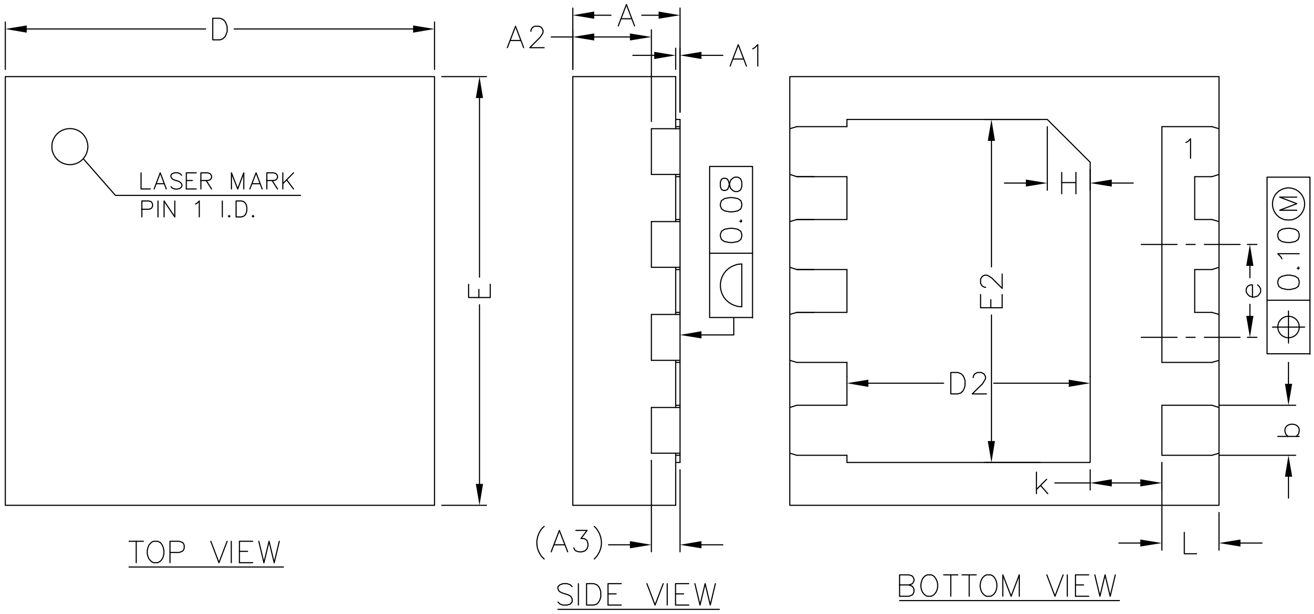
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

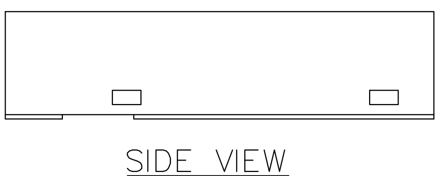


Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case





COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
A2	0.50	0.55	0.60
A3	0.20REF		
b	0.30	0.35	0.40
D	2.90	3.00	3.10
E	2.90	3.00	3.10
D2	1.60	1.70	1.80
E2	2.30	2.40	2.50
e	0.55	0.65	0.75
K	0.40	0.50	0.60
L	0.35	0.40	0.45

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Din-Tek Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Din-Tek”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Din-Tek makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Din-Tek disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Din-Tek’s knowledge of typical requirements that are often placed on Din-Tek products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer’s responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer’s technical experts. Product specifications do not expand or otherwise modify Din-Tek’s terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Din-Tek products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Din-Tek product could result in personal injury or death. Customers using or selling Din-Tek products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Din-Tek personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Din-Tek. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Din-Tek Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Din-Tek documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Din-Tek Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Din-Tek documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.